

# **Excellent Integrated System Limited**

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NXP Semiconductors/Freescale Semiconductor, Inc. PMEG4020EPK,315

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### 1. General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a leadless ultra small DFN1608D-2 (SOD1608) Surface-Mounted Device (SMD) plastic package with visible and solderable side pads.

### 2. Features and benefits

- Average forward current: I<sub>F(AV)</sub> ≤ 2 A
- Reverse voltage: V<sub>R</sub> ≤ 40 V
- Low forward voltage V<sub>F</sub> ≤ 660 mV
- Low reverse current
- AEC-Q101 qualified
- Solderable side pads
- Package height typ. 0.37 mm
- Ultra small and leadless SMD plastic package

# 3. Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch mode power supply
- LED backlight for mobile application
- Low power consumption applications
- Ultra high-speed switching
- Reverse polarity protection

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; $T_{sp} \le$ 130 °C; square wave		-	-	2	Α
		$\delta$ = 0.5; f = 20 kHz; $T_{amb} \le 25$ °C; square wave	[1]	-	-	2	А
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	-	40	V
V <sub>F</sub>	forward voltage	$I_F$ = 2 A; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C		-	585	660	mV





Datasheet of PMEG4020EPK,315 - DIODE SCHOTTKY 40V 2A 2DFN

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#### 40 V, 2 A low VF MEGA Schottky barrier rectifier

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>R</sub>	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	1	5	μΑ
t <sub>rr</sub>	reverse recovery time	$I_R = 0.5 \text{ A}; I_F = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4	-	ns

<sup>[1]</sup> Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode[1]		1 <del>][-]</del> 2
2	A	anode	1 2	sym001
			Transparent top view DFN1608D-2 (SOD1608)	

<sup>[1]</sup> The marking bar indicates the cathode.

# 6. Ordering information

Table 3. Ordering information

Type number	per Package				
	Name	Description	Version		
PMEG4020EPK	DFN1608D-2	DFN1608D-2: leadless ultra small plastic package; 2 terminals	SOD1608		

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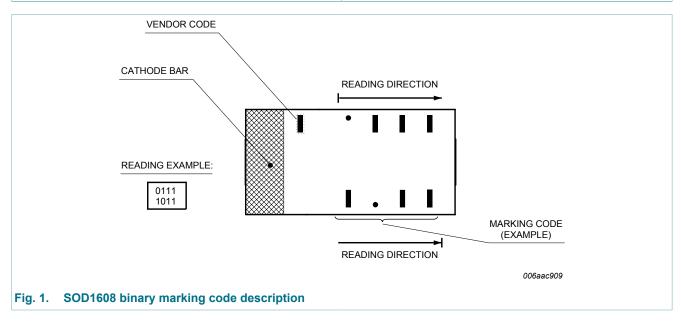
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# 7. Marking

Table 4. Marking codes

Type number	Marking code
PMEG4020EPK	0001 0000



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### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>R</sub>	reverse voltage	T <sub>j</sub> = 25 °C		-	40	V
I <sub>F</sub>	forward current	T <sub>sp</sub> ≤ 125 °C		-	2.83	Α
I <sub>F(AV)</sub>	average forward current	$\delta$ = 0.5; f = 20 kHz; T <sub>sp</sub> ≤ 130 °C; square wave		-	2	А
		$\delta$ = 0.5; f = 20 kHz; $T_{amb} \le$ 25 °C; square wave	[1]	-	2	А
I <sub>FRM</sub>	repetitive peak forward current	$t_p \le 1 \text{ ms}; \ \delta \le 0.25$		-	4	Α
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 8 ms; $T_{j(init)}$ = 25 °C; square wave		-	5	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[2]	-	415	mW
			[3]	-	895	mW
			[1]	-	1565	mW
T <sub>j</sub>	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- [1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.

### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub> thermal resistance from junction to ambient		in free air	[1][2]	-	-	300	K/W
		[1][3]	-	-	140	K/W	
	ambient		[1][4]	-	-	80	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point		[5]	-	-	20	K/W

- [1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P<sub>R</sub> are a significant part of the total power losses.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm<sup>2</sup>.
- [4] Device mounted on a ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint.
- [5] Soldering point of cathode tab.

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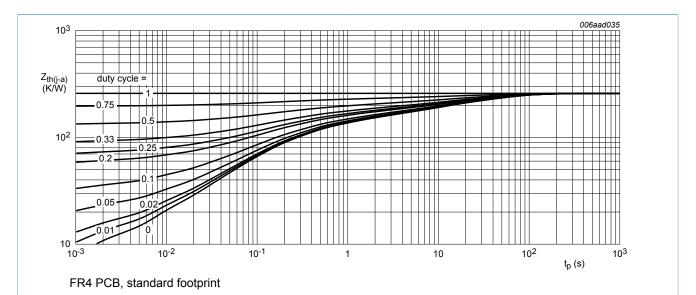
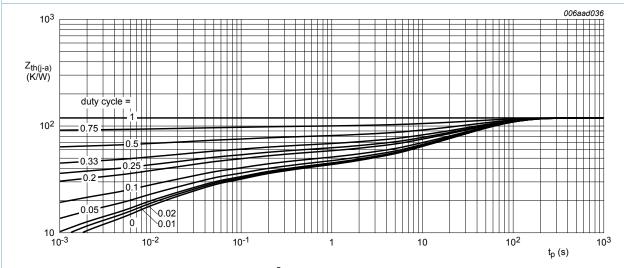


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

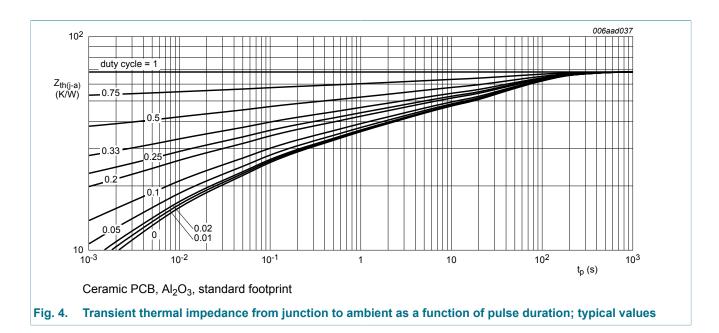


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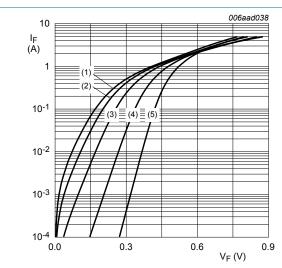
### 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>F</sub>	forward voltage	$I_F$ = 100 mA; pulsed; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 25 °C	-	330	380	mV
		$I_F$ = 500 mA; pulsed; $t_p \le 300 \ \mu s$ ; $\delta \le 0.02$ ; $T_j$ = 25 °C	-	415	480	mV
		$I_F$ = 1 A; pulsed; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 25 °C	-	490	550	mV
		$I_F$ = 2 A; pulsed; $t_p \le 300$ μs; $δ \le 0.02$ ; $T_j$ = 25 °C	-	585	660	mV
I <sub>R</sub> reve	reverse current	V <sub>R</sub> = 10 V; T <sub>j</sub> = 25 °C	-	1	5	μA
		V <sub>R</sub> = 40 V; T <sub>j</sub> = 25 °C	-	8	30	μA
C <sub>d</sub>	diode capacitance	V <sub>R</sub> = 1 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	75	90	pF
		V <sub>R</sub> = 10 V; f = 1 MHz; T <sub>j</sub> = 25 °C	-	30	40	pF
t <sub>rr</sub>	reverse recovery time	$I_F = 0.5 \text{ A}; I_R = 0.5 \text{ A}; I_{R(meas)} = 0.1 \text{ A};$ $T_j = 25 \text{ °C}$	-	4	-	ns
$V_{FRM}$	peak forward recovery voltage	$I_F = 0.5 \text{ A}; dI_F/dt = 20 \text{ A/}\mu\text{s}; T_j = 25 ^{\circ}\text{C}$	-	440	-	mV

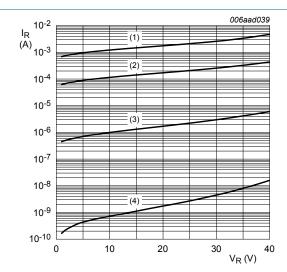
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- (1)  $T_i = 150 \, ^{\circ}C$
- (2)  $T_j = 125 \, ^{\circ}C$
- (3)  $T_i = 85 \,^{\circ}C$
- (4)  $T_i = 25 \, ^{\circ}C$
- (5)  $T_i = -40 \, ^{\circ}C$

Fig. 5. Forward current as a function of forward voltage; typical values



- (1)  $T_i = 125 \,^{\circ}C$
- (2)  $T_i = 85 \, ^{\circ}C$
- (3)  $T_j = 25 \, ^{\circ}C$
- (4)  $T_i = -40 \, ^{\circ}\text{C}$

Fig. 6. Reverse current as a function of reverse voltage; typical values

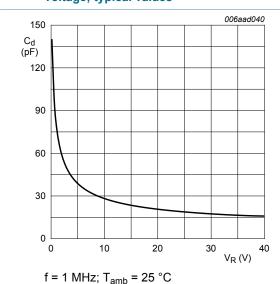
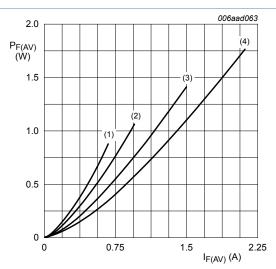


Fig. 7. Diode capacitance as a function of reverse voltage; typical values



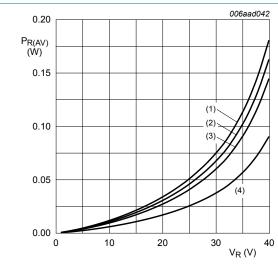
- T<sub>i</sub> = 150 °C
- $(1) \delta = 0.1$
- $(2) \delta = 0.2$
- $(3) \delta = 0.5$
- $(4) \delta = 1$

Fig. 8. Average forward power dissipation as a function of average forward current; typical values

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T<sub>i</sub> = 125 °C

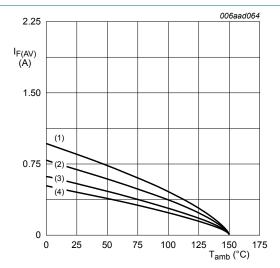
 $(1) \delta = 1$ 

 $(2) \delta = 0.9$ 

 $(3) \delta = 0.8$ 

 $(4) \delta = 0.5$ 

Fig. 9. Average reverse power dissipation as a function of reverse voltage; typical values



FR4 PCB, standard footprint

 $T_i = 150 \,{}^{\circ}\text{C}$ 

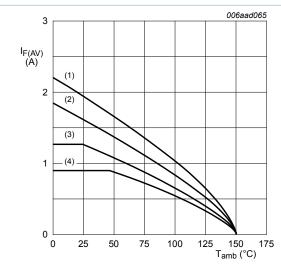
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta$  = 0.1; f = 20 kHz

Fig. 10. Average forward current as a function of ambient temperature; typical values



FR4 PCB, mounting pad for cathode 1 cm<sup>2</sup>

 $T_j$  = 150 °C

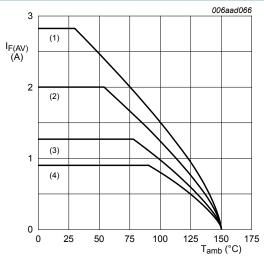
(1)  $\delta = 1$  (DC)

(2)  $\delta = 0.5$ ; f = 20 kHz

(3)  $\delta = 0.2$ ; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 11. Average forward current as a function of ambient temperature; typical values



Ceramic PCB, Al<sub>2</sub>O<sub>3</sub>, standard footprint

T<sub>i</sub> = 150 °C

(1)  $\delta = 1$  (DC)

(2)  $\delta$  = 0.5; f = 20 kHz

(3)  $\delta$  = 0.2; f = 20 kHz

(4)  $\delta = 0.1$ ; f = 20 kHz

Fig. 12. Average forward current as a function of ambient temperature; typical values

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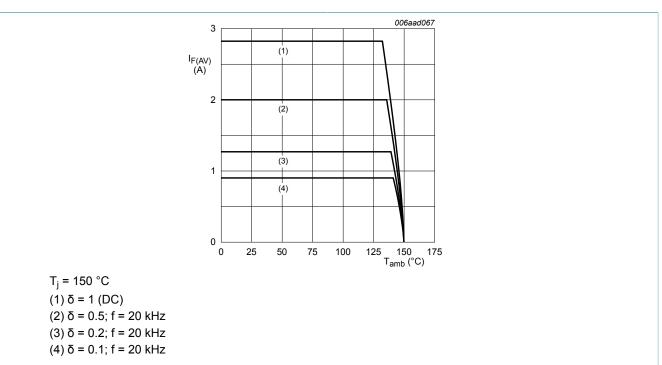


Fig. 13. Average forward current as a function of solder point temperature; typical values

### 11. Test information

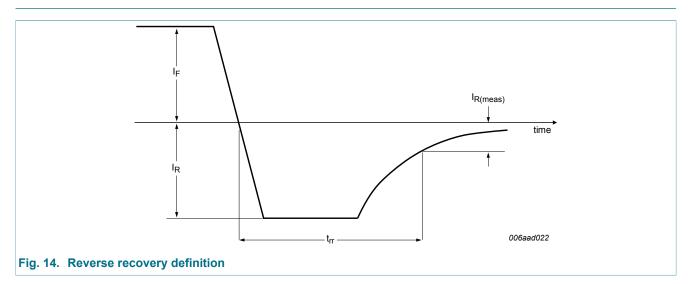
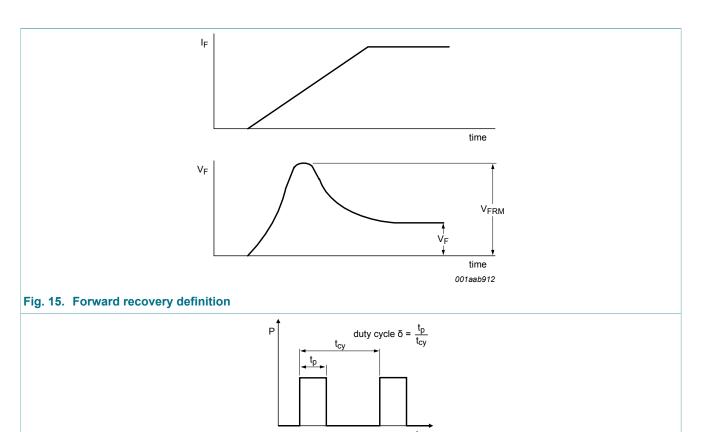




Fig. 16. Duty cycle definition

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The current ratings for the typical waveforms are calculated according to the equations:  $I_{F(AV)} = I_M \times \delta$  with  $I_M$  defined as peak current,  $I_{RMS} = I_{F(AV)}$  at DC, and  $I_{RMS} = I_M \times \sqrt{\delta}$  with  $I_{RMS}$  defined as RMS current.

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### 11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

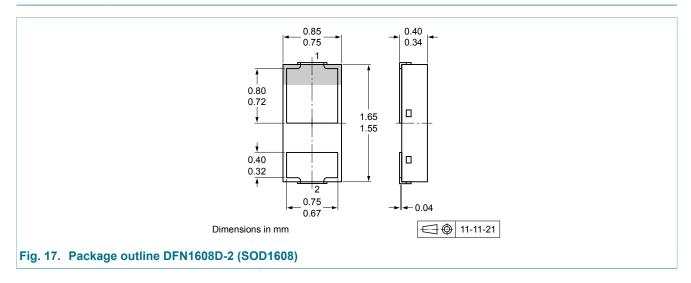
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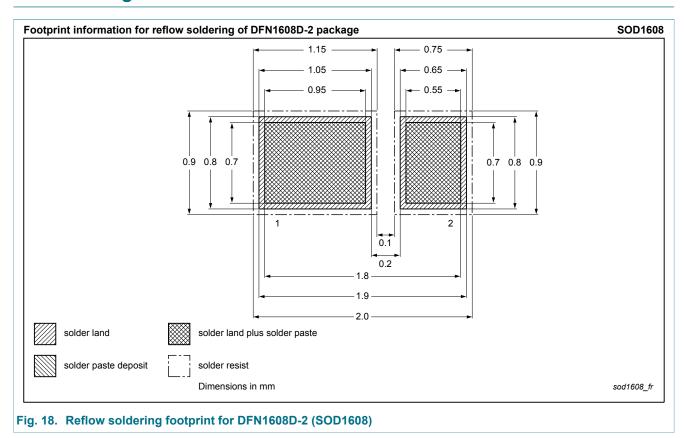
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### 12. Package outline



# 13. Soldering



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# 14. Revision history

#### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PMEG4020EPK v.2	20140211	Product data sheet	-	PMEG4020EPK v.1		
Modifications:	ations: • Marking code corrected					
PMEG4020EPK v.1	20120425	Product data sheet	-	-		



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### 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 11 February 2014

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